V_{RSM}	V_{RRM} V_{DRM}	I_{TRMS} =95A(maximum value for continous operation)		
V	V	I_{TAV} =55A(sin.180; Tc=80℃)		
500	400		SKKH 56/04D	
700	600	SKKT 56/06E	SKKH 56/06D	
900	800	SKKT 56/08E	SKKH 56/08D	
1300	1200	SKKT 56/12E	SKKH 56/12E	
1500	1400	SKKT 56/14E	SKKH 56/14E	
1700	1600	SKKT 56/16E	SKKH 56/16E	
1900	1800	SKKT 56/18E	SKKH 56/18E	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; Tc = 85(100)℃;	50(35)	A
I_D	P3/180 ; Ta = 45℃; B2 / B6	57 / 68	A
	P3/180F; Ta = 35℃; B2 / B6	100 / 130	A
I_{RMS}	P3/180F; Ta = 35℃; W1 / W3	130 / 3 * 100	A
I_{TSM}	T_{vj} = 25℃; 10ms	1500	A
	T_{vj} = 125℃; 10ms	1250	A
i^2t	T_{vj} = 25℃; 8，3 ...10ms	11000	A^2S
	T_{vj} = 125℃; 8，3 ...10ms	8000	A^2S
V_T	T_{vj} = 25℃; I_T=168A	max.1.65	V
$V_{T(TO)}$	T_{vj} = 125℃	max.0.9	V
r_T	T_{vj} = 125℃	max.3.5	mΩ
I_{DD};I_{RD}	T_{vj} = 125℃; V_{RD}=V_{RRM} ; V_{DD}=V_{DRM}	max.15	mA
t_{gd}	T_{vj} = 25℃; I_G = 1A; di$_G$/dt = A/μs	1	μs
t_{gr}	V_D = 0.67*V_{DRM}	2	μs
$(di/dt)_{cr}$	T_{vj} = 125℃	max.150	A/μs
$(dv/dt)_{cr}$	T_{vj} = 125℃ ; SKKT...D / SKK...E	max.500 / 1000	V/μs
t_q	T_{vj} = 125℃	250	μs
I_H	T_{vj} = 25℃ ; typ./max	150 / 250	mA
I_L	T_{vj} = 25℃ ; RG = 33Ω ; typ./max	300 / 600	mA
V_{GT}	T_{vj} = 25℃ ; d.c.	min. 3	V
I_{GT}	T_{vj} = 25℃ ; d.c.	min. 150	mA
V_{GD}	T_{vj} = 125℃ ; d.c.	max. 0.25	V
I_{GD}	T_{vj} = 125 ℃ ; d.c.	max. 6	mA
$R_{th(j-c)}$	cont.; per thyristor/per module	0.57 / 0.29	K/W
$R_{th(j-c)}$	sin. 180; per thyristor/per module	0.6 / 0.3	K/W
$R_{th(j-c)}$	rec. 120; per thyristor/per module	0.64 / 0.32	K/W
$R_{th(j-c)}$	per thyristor/per module	0.2 / 0.1	K/W
T_{vj}		- 40...+ 125	℃
T_{stg}		- 40...+ 125	℃
V_{isol}	a. c. 50Hz; r.m.s. ; 1s/1min	3600/3000	V~
M_s	to heatsink	5 ± 15%[1])	Nm
M_t	to terminal	3 ± 15%	Nm
a		5 * 9.81	m/s^2
m	approx.	95	g
Case	SKKT	LJ1	

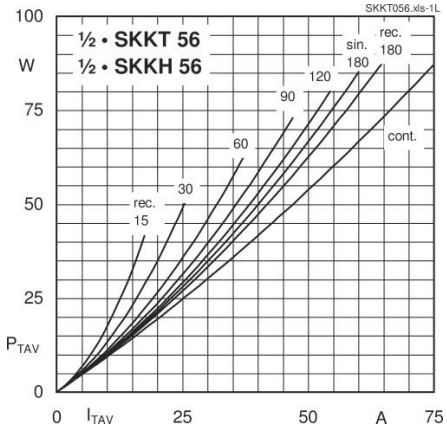


Fig. 1L Power dissipation per thyristor vs. on-state current

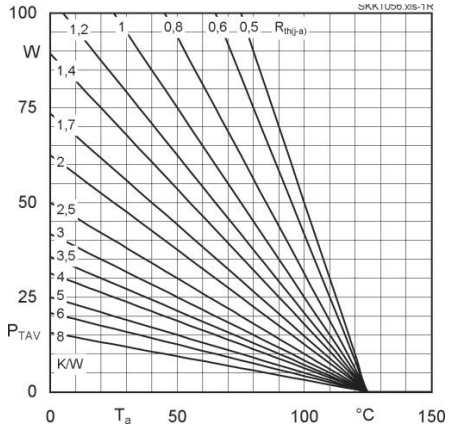


Fig. 1R Power dissipation per thyristor vs. ambient temp.

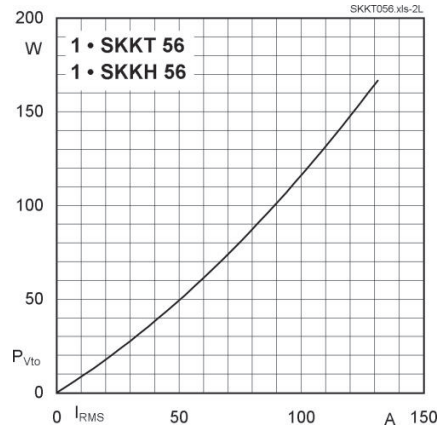


Fig. 2L Power dissipation per module vs. rms current

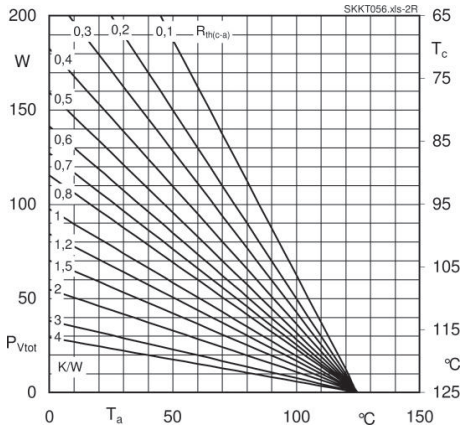


Fig. 2R Power dissipation per module vs. case temp.

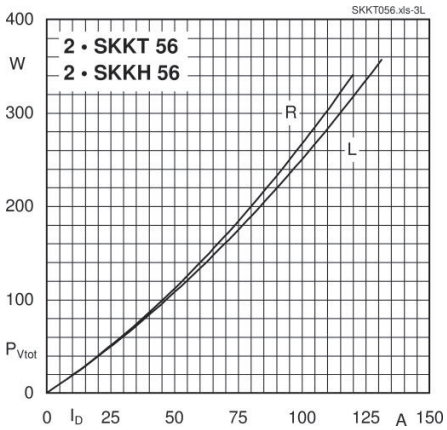


Fig. 3L Power dissipation of two modules vs. direct current

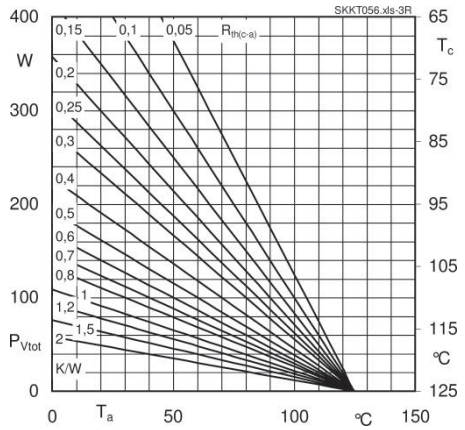


Fig. 3R Power dissipation of two modules vs. case temp.

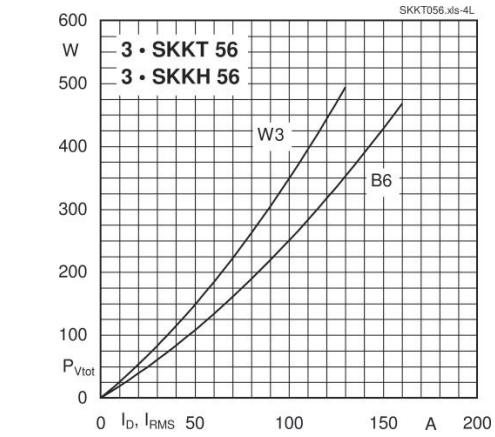


Fig. 4L Power dissipation of three modules vs. direct and rms current

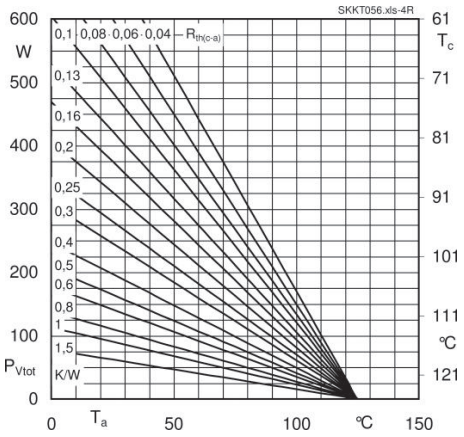


Fig. 4R Power dissipation of three modules vs. case temp.

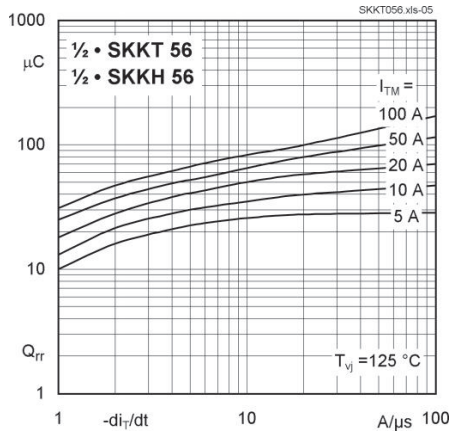


Fig. 5 Recovered charge vs. current decrease

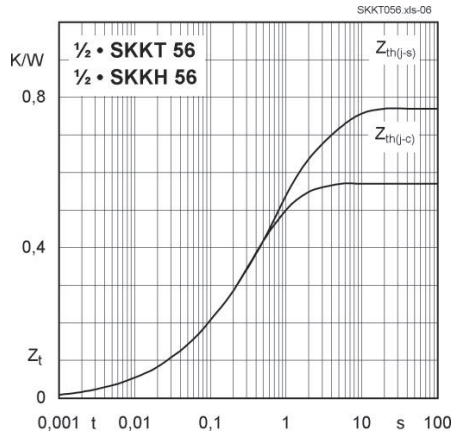


Fig. 6 Transient thermal impedance vs. time

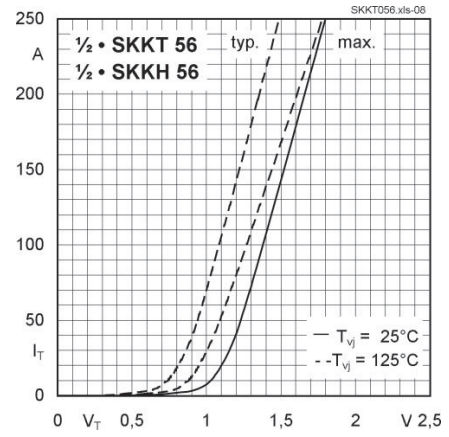


Fig. 7 On-state characteristics

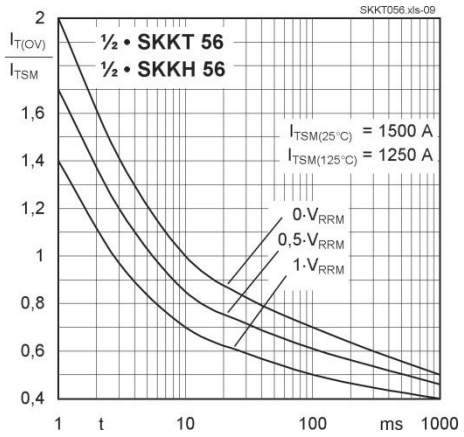
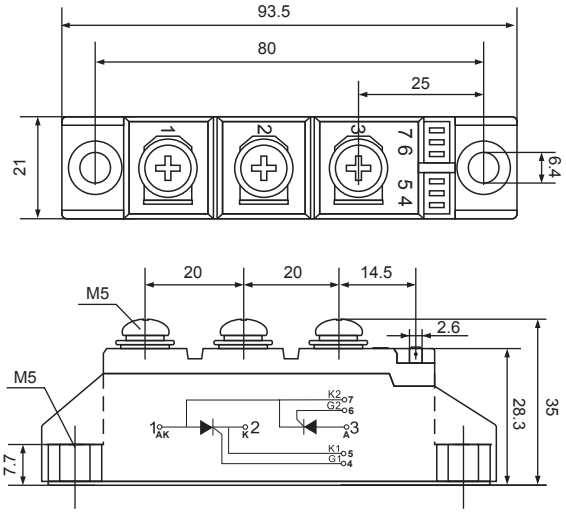


Fig. 8 Surge overload current vs. time



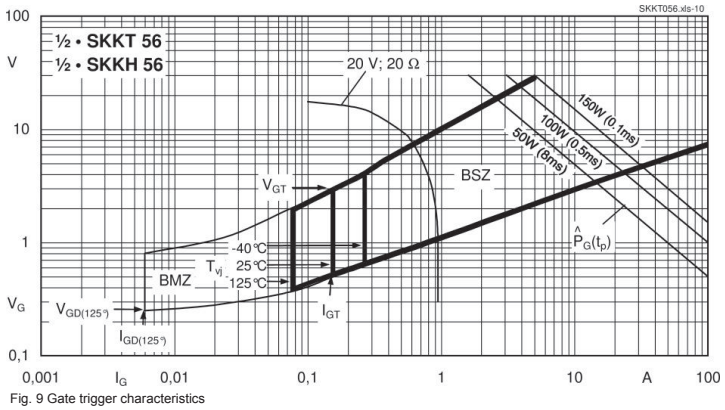


Fig. 9 Gate trigger characteristics

4006606086@B.QQ.COM

ZHEJIANG LIUJING RECTIFIER CO., LTD
Sale Departmant: Liujing Building, Yueqing City, Zhejiang Province
Add: Wanao Industrial Zone, Yueqing city, Zhejiang Province
Tel: 0086-577-62519692 0089-577-62519693
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